



Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER HIRA.0204	SERIAL NUMBER 10/549,683
	APPLICANT SUDA et al.	
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U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
						YES	NO

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

	Norio Onojima et al., "High-Quality AIN by Initial Layer-by-Layer Growth on Surface-Controlled 4H-SiC(0001) Substrate", Jpn. J. Appl. Phys. Vol. 42, Part 2, No. 5A (May 1, 2003), pp. L445-L447.
	N. Onojima et al., "Impact of SiC Surface Control on Initial Growth Mode and Crystalline Quality of AIN Grown by Molecular-Beam Epitaxy", Phys. Stat. Sol. (c) 0, No. 7 (2003), pp. 2529-2532/DOI 10.1002/pssc.200303358.
	Jun Suda et al., "Either Step-Flow or Layer-by-Layer Growth for AIN on SiC (0001) Substrates", Mat. Res. Soc. Symp. Proc., Vol. 798 (2004), © Materials Research Society, pp. Y3.4.1-Y3.4.6.

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EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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